



AOP605

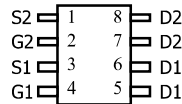
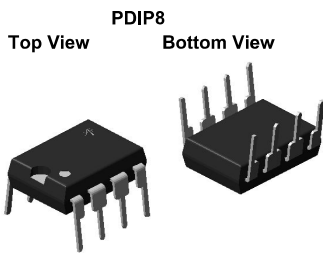
Complementary Enhancement Mode Field Effect Transistor

General Description

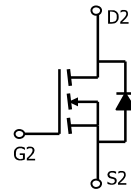
The AOP605/L uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. The complementary MOSFETs form a high-speed power inverter, suitable for a multitude of applications. AOP605 and AOP605L are electrically identical.
-RoHS Compliant
-AOP605L is Halogen Free

Features

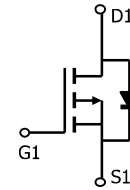
n-channel	p-channel
V_{DS} (V) = 30V	-30V
I_D = 7.5A (V_{GS} = 10V)	-6.6A (V_{GS} = -10V)
$R_{DS(ON)}$	
< 28m Ω (V_{GS} = 10V)	< 35m Ω (V_{GS} = -10V)
< 43m Ω (V_{GS} = 4.5V)	< 58m Ω (V_{GS} = -4.5V)



PDIP-8



n-channel



p-channel

Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Max n-channel	Max p-channel	Units
Drain-Source Voltage	V_{DS}	30	-30	V
Gate-Source Voltage	V_{GS}	± 20	± 20	V
Continuous Drain Current ^A	I_D	$T_A=25^\circ\text{C}$	7.5	-6.6
		$T_A=70^\circ\text{C}$	6	-5.3
Pulsed Drain Current ^B	I_{DM}	30	-30	A
Power Dissipation	P_D	$T_A=25^\circ\text{C}$	2.5	2.5
		$T_A=70^\circ\text{C}$	1.6	1.6
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	-55 to 150	$^\circ\text{C}$

Thermal Characteristics: n-channel

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	40	50	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^A		Steady-State	67	80
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	33	40	$^\circ\text{C/W}$

Thermal Characteristics: p-channel

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	38	50	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^A		Steady-State	66	80
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	30	40	$^\circ\text{C/W}$